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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/643,004
Filing Date August 21, 2000
Inventor Gary A. Mercaldi
Assignee Micron Technology, Inc.
Group Art Unit 2823
Examiner T. Dang
Attorney's Docket No. MI22-1358
Title: Low Selectivity Deposition Methods

RESPONSE TO AUGUST 27, 2002 OFFICE ACTION

To: Box Non Fee Amendment
Assistant Commissioner for Patents
Washington, D.C. 20231

From: James E. Lake (Tel. 509-624-4276; Fax 509-838-3424)
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AMENDMENTSIn the Specification

Please replace the paragraph beginning at line 8 of page 20 with the following
clean replacement paragraph in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

a' --Further, forming a deposition layer may occur by unconventional CVD in a process regime so far outside conventional CVD that the deposition is substantially selective. That is, multiple deposition species may contact the substrate together in the deposition chamber. However, temperature and pressure are low enough that the thickness of the deposition layer over a first part of a substrate is less than 50% of a thickness of the deposition layer over a second part, as shown in Fig. 2. Exemplary parameters include

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